TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

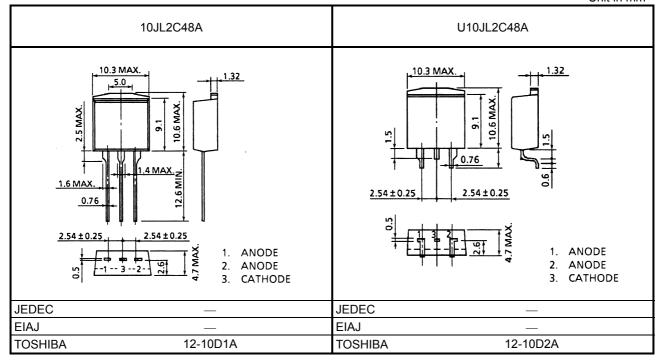
10JL2C48A,U10JL2C48A

SWITCHING MODE POWER SUPPLY APPLICATION **CONVERTER & CHOPPER APPLICATION**

Repetitive Peak Reverse Voltage $: V_{RRM} = 600V$ Average Output Rectified Current $: I_O = 10A$ Ultra Fast Reverse-Recovery Time : $t_{rr} = 35ns$ (Max.)

Low Switching Losses and Output Noise.

Unit in mm



The information contained herein is subject to change without notice.

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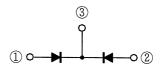
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MAXIMUM RATINGS

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CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V _{RRM}	600	V
Average Output Rectified Current	IO	10	Α
Peak One Cycle Surge Forward Current (Non-Repetitive, Sine Wave)	IFSM	40	Α
Junction Temparature	Tj	-40~150	°C
Storage Temparature Range	T _{stg}	-40~150	°C

POLARITY

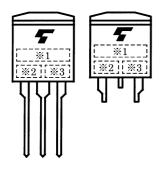


ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	(Note)	VFM	I _{FM} = 5A	_	_	4.0	V
Repetitive Peak Reverse Current	(Note)	IRRM	V _{RRM} = 600V	_	_	50	μΑ
Reverse Recovery Time	(Note)	t _{rr}	I _F = 2A, di / dt = -20A / μs	_	_	35	ns
Junction Capacitance		C _j	V _R = 10V, f = 1.0MHz	_	36	_	pF
Thermal Resistance		Rth (j-c)	DC Total	_	_	2.5	°C/W

Note: A value of one cell.

MARKING



* 1	MARK	10JL2C	TYPE	10JL2C48A, U10JL2C48A				
* 2	Α							
* 3	Lot Number Month (Starting from Alphabet A)							

